

Silicon NPN Power Transistors

2SC1079 2SC1080

DESCRIPTION

- With TO-3 package
- Complement to type 2SA679/680
- High power dissipation

APPLICATIONS

- For audio power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

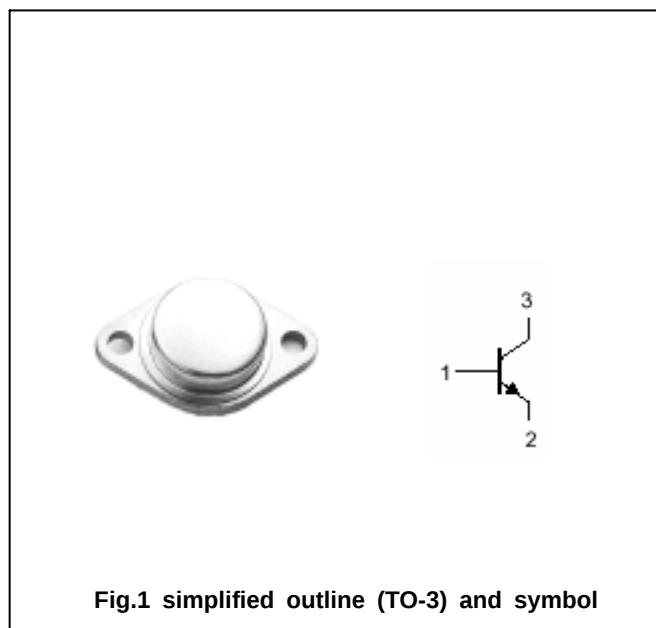


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = -$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SC1079	Open emitter	120	V
		2SC1080		100	
V_{CEO}	Collector-emitter voltage	2SC1079	Open base	120	V
		2SC1080		100	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			12	A
I_E	Emitter current			-12	A
P_C	Collector power dissipation		$T_C = 25$	100	W
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-65~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SC1079	$I_C=0.1A ; I_B=0$	120			V
		2SC1080		100			
$V_{(BR)EBO}$	Emitter-base breakdown voltage		$I_E=10mA ; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage		$I_C=10A ; I_B=1A$			3.0	V
V_{BE}	Base-emitter on voltage		$I_C=10A ; V_{CE}=5V$			2.5	V
I_{CBO}	Collector cut-off current		$V_{CB}=50V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current		$V_{EB}=5V ; I_C=0$			0.1	mA
h_{FE-1}	DC current gain		$I_C=2A ; V_{CE}=5V$	40		140	
h_{FE-2}	DC current gain		$I_C=7A ; V_{CE}=5V$	15			
f_T	Transition frequency		$I_C=2A ; V_{CE}=5V$		4		MHz

◆ h_{FE-1} Classifications

R	Y
40-80	70-140

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PACKAGE OUTLINE

